

isc N-Channel MOSFET Transistor

2SK1632

DESCRIPTION

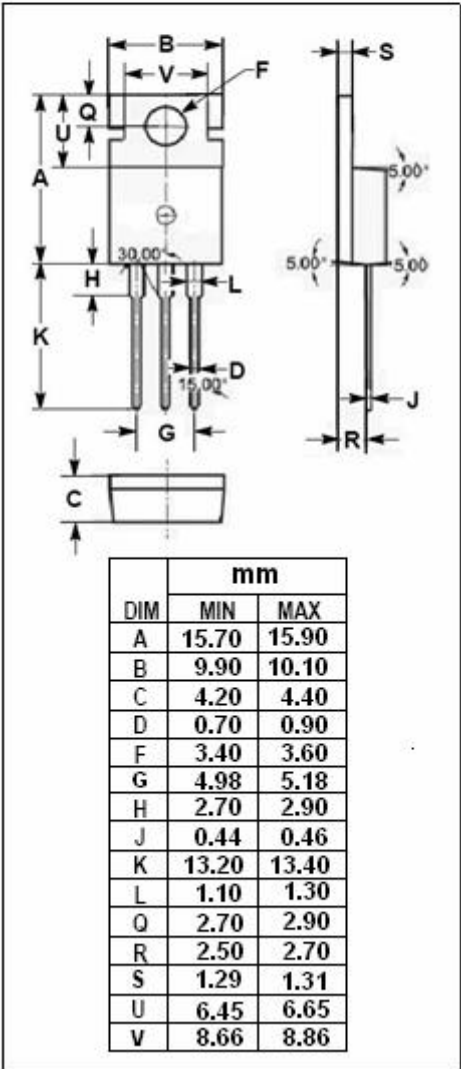
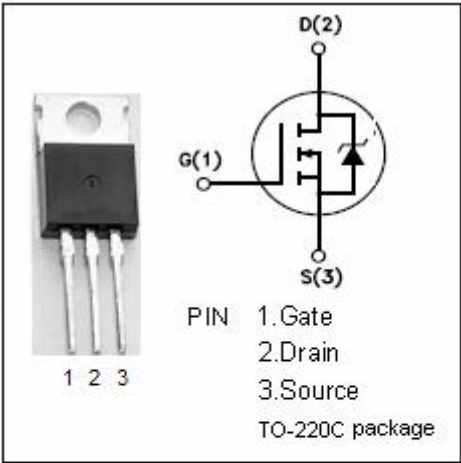
- Drain Current $-I_D = 5A @ T_C = 25^{\circ}C$
- Drain Source Voltage-
: $V_{DSS} = 700V (Min)$

APPLICATIONS

- Designed for high voltage, high speed power switching applications such as switching regulators, converters, solenoid and relay drivers.

ABSOLUTE MAXIMUM RATINGS($T_a = 25^{\circ}C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage ($V_{GS} = 0$)	700	V
V_{GS}	Gate-Source Voltage	± 30	V
I_D	Drain Current-continuous@ $T_C = 25^{\circ}C$	5	A
P_{tot}	Total Dissipation@ $T_C = 25^{\circ}C$	150	W
T_j	Max. Operating Junction Temperature	150	$^{\circ}C$
T_{stg}	Storage Temperature Range	-55~150	$^{\circ}C$



isc N-Channel Mosfet Transistor**2SK1632****• ELECTRICAL CHARACTERISTICS (T_C=25°C)**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0; I _D = 10mA	700			V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =10 V _{GS} ; I _D =1mA	2.0	3.0	4.0	V
R _{DS(on)}	Drain-Source On-stage Resistance	V _{GS} =10V; I _D =3A			2.3	Ω
I _{GSS}	Gate Source Leakage Current	V _{GS} = ±30V; V _{DS} = 0			±100	nA
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =700V; V _{GS} = 0			500	uA